



DOCUMENT CHANGE REQUEST

DCR number 1218 Changes required for: General

Date: 2019/07/04

Date sent: 2019/01/22

Originator: Steve Jeffery

Organisation: ESCC Executive

Status: IMPLEMENTED

Title: Diodes, Silicon, Power Rectifier , High Efficiency, Fast Recovery, based on type BYW81-200

Number: 5103/029

Issue: 11

Other documents affected:

5103/030-8, 5103/031-9, 5103/032-2, 5106/016-9, 5106/017-6, 5106/018-7, 5106/019-8, 5203/010-8, 5204/002-8, 5205/023-6, 5205/024-5

Page:

As applicable

Paragraph:

The Deviations from Qualification and Periodic Tests - Chart F4 paragraph of the relevant Detail Specs.

Original wording:

See each detail specs Deviations from Qualification and Periodic Tests - Chart F4 paragraph.

Proposed wording:

As described in the attached excel file STM DCR to remove deviations.xlsx

Justification:

The qualified manufacturer ST has confirmed that, for these Detail Specs for diodes, transistors and power MOSFETs, the existing deviations from Chart F4 should be removed (i.e. Constant Acceleration and Terminal Strength are performed as part of ESCC 5000 Chart F4A – Qualification, Periodic Testing and Lot Validation Testing for Packaged Components.)

See also DCR 1199.

A related editorial DCR against ESCC Generic Spec No. 5000 is related to this DCR and DCR 1199.

Attachments:

stm_dcr_to_remove_deviations.xlsx

Modifications:

The following Modification wording shall be added to DCR (change proposed by CNES, and commented by mfr ST - see also ESCC 5106/023 issue 1 update per DCR 1199 - the specified Junction temperature Test Condition for B-1 & Op Life should be the max. Rating for TJ given in Para. 1.5 of the spec)

An additional change is required as follows for Detail Specification ESCC 5102/032 issue 1:

Page 11. para 2.7(Power Burn-in Conditions):

The Junction Temperature Test Condition is corrected from "+150(+0 -5) to "
+175(+0 -5)"

Approval signature:



Date signed:

2019-07-04